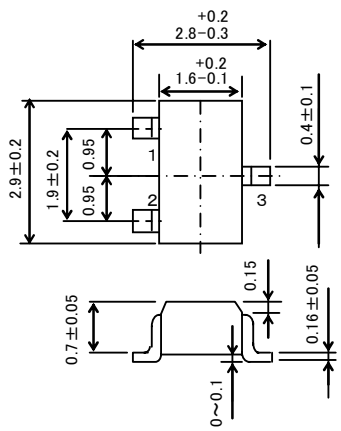
TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type

SSM3K310T

High-Speed Switching Applications

- 1.5 V drive
- Low ON-resistance: R_{on} = 66 mΩ (max) (@V_{GS} = 1.5 V)
  R_{on} = 43 mΩ (max) (@V_{GS} = 1.8 V)
  R_{on} = 32 mΩ (max) (@V_{GS} = 2.5 V)
  R_{on} = 28 mΩ (max) (@V_{GS} = 4.0 V)

Unit: mm



TSM

1.GATE
2.SOURCE
3.DRAIN

JEDEC	—
JEITA	—
TOSHIBA	2-3S1A

Weight: 10 mg (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DS}	20	V
Gate-Source voltage		V_{GSS}	± 10	V
Drain current	DC	I_D	5.0	A
	Pulse	I_{DP}	10.0	
Drain power dissipation		$P_{D\ (Note\ 1)}$	700	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55~150	°C

Note 1: Mounted on an FR4 board.
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 645 mm^2)

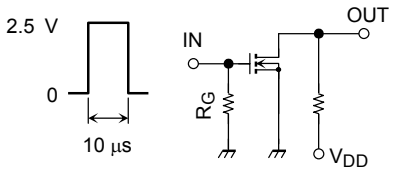
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain-Source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 1 mA, V_{GS} = 0	20	—	—	V
		$V_{(BR)\ DSX}$	I_D = 1 mA, V_{GS} = −10 V	12	—	—	
Drain cutoff current		I_{DSS}	V_{DS} = 20 V, V_{GS} = 0	—	—	1	μA
Gate leakage current		I_{GSS}	V_{GS} = ±10 V, V_{DS} = 0	—	—	±1	μA
Gate threshold voltage		V_{th}	V_{DS} = 3 V, I_D = 1 mA	0.35	—	1.0	V
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 3 V, I_D = 4.0 A (Note 2)	14	28	—	S
Drain-Source ON-resistance		$R_{DS\ (ON)}$	I_D = 4.0 A, V_{GS} = 4.0 V (Note 2)	—	19	28	mΩ
			I_D = 3.0 A, V_{GS} = 2.5 V (Note 2)	—	23	32	
			I_D = 1.0 A, V_{GS} = 1.8 V (Note 2)	—	28	43	
			I_D = 0.5 A, V_{GS} = 1.5 V (Note 2)	—	33	66	
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0, f = 1 MHz	—	1120	—	pF
Output capacitance		C_{oss}		—	180	—	
Reverse transfer capacitance		C_{rss}		—	160	—	
Total Gate Charge		Q_g	V_{DS} = 10 V, I_{DS}= 5.0 A V_{GS} = 4 V	—	14.8	—	nC
Gate-Source Charge		Q_{gs}		—	11.4	—	
Gate-Drain Charge		Q_{gd}		—	3.4	—	
Switching time	Turn-on time	t_{on}	V_{DD} = 10 V, I_D = 2.0 A, V_{GS} = 0~2.5 V, R_G = 4.7 Ω	—	21	—	ns
	Turn-off time	t_{off}		—	36	—	
Drain-Source forward voltage		V_{DSF}	I_D = −5.0 A, V_{GS} = 0 V (Note 2)	—	-0.85	-1.2	V

Note 2: Pulse test

Switching Time Test Circuit

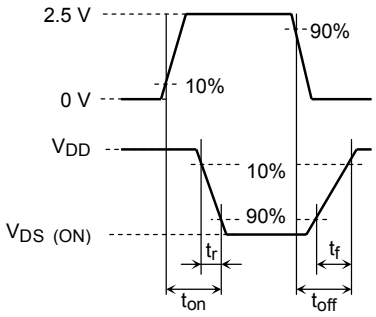
(a) Test Circuit



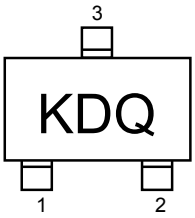
V_{DD} = 10 V
R_G = 4.7 Ω
D.U. ≦ 1%
V_{IN}: t_r, t_f < 5 ns
Common Source
Ta = 25°C

(b) V_{IN}

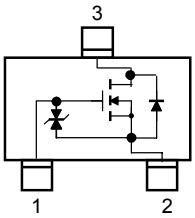
(c) V_{OUT}



Marking



Equivalent Circuit (top view)



Notice on Usage

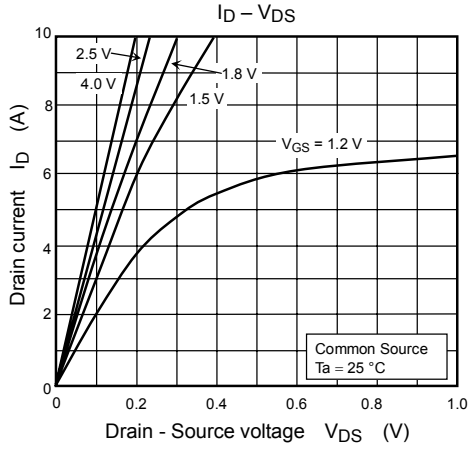
V_{th} can be expressed as the voltage between gate and source when the low operating current value is I_D = 1 mA for this product. For normal switching operation, $V_{GS\ (on)}$ requires a higher voltage than V_{th}, and $V_{GS\ (off)}$ requires a lower voltage than V_{th}. (The relationship can be established as follows: $V_{GS\ (off)} < V_{th} < V_{GS\ (on)}$.)

Take this into consideration when using the device.

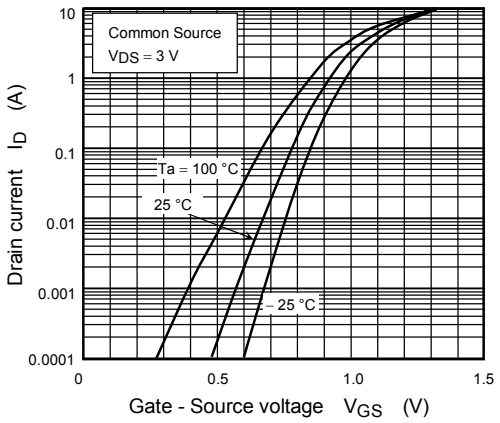
Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.

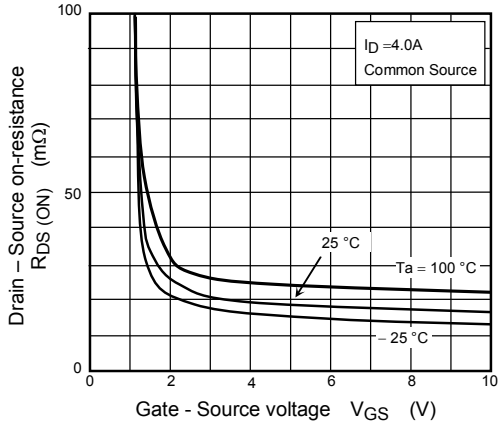
I_D – V_{DS}



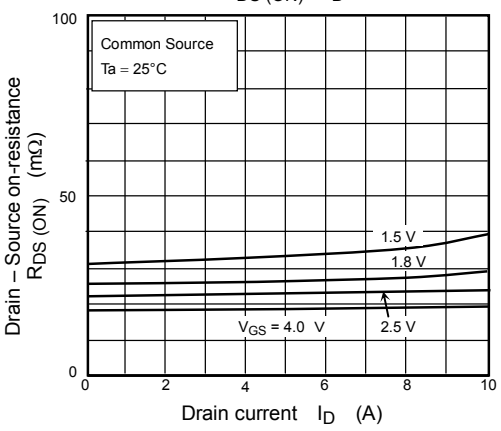
I_D – V_{GS}



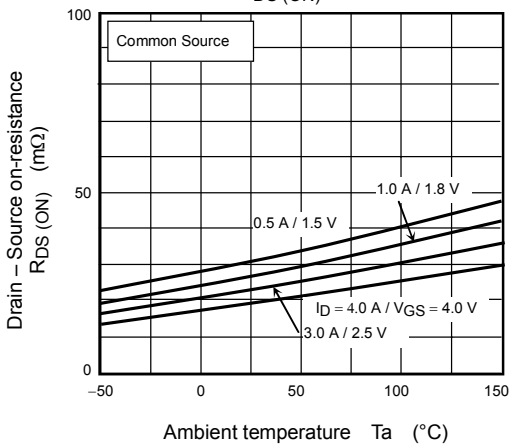
$R_{DS\ (ON)}$ – V_{GS}



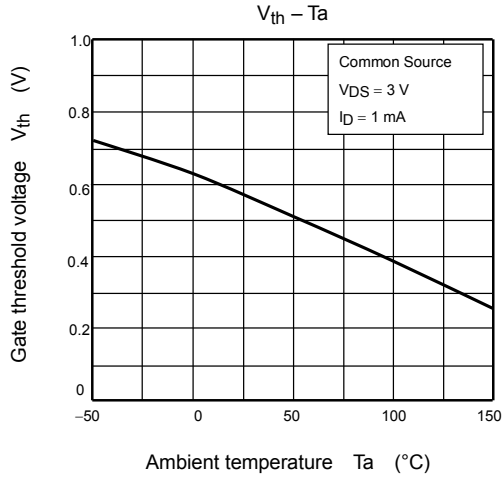
$R_{DS\ (ON)}$ – I_D



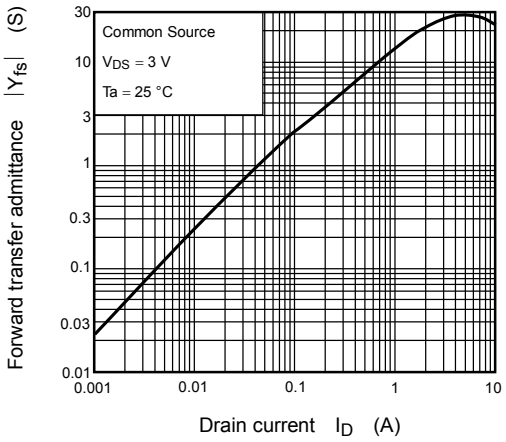
$R_{DS\ (ON)}$ – Ta



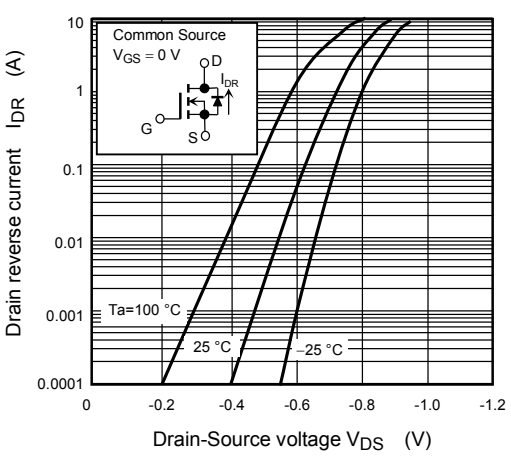
V_{th} – Ta



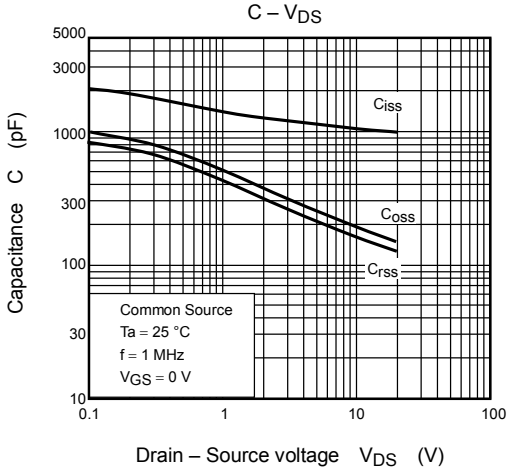
$|Y_{fs}| - I_D$



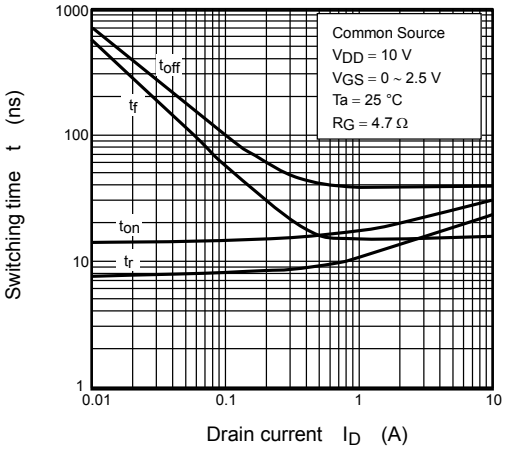
$I_{DR} - V_{DS}$



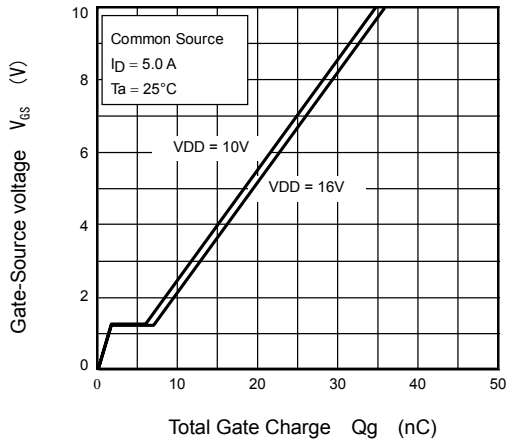
$C - V_{DS}$



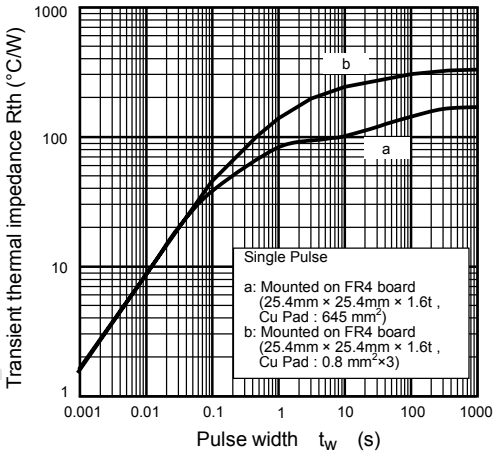
$t - I_D$



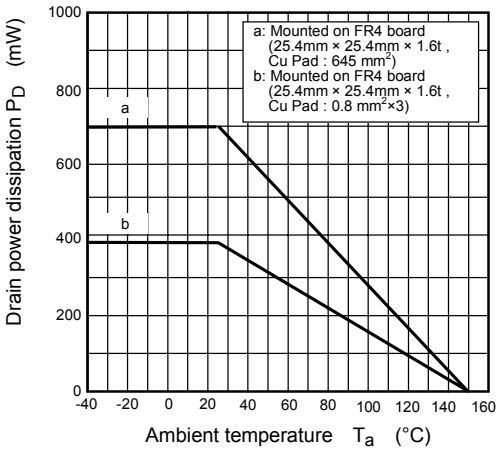
Dynamic Input Characteristic



$r_{th} - t_w$



$P_D - T_a$



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